

# Investigation of the time resolution of unirradiated and irradiated 3D sensors

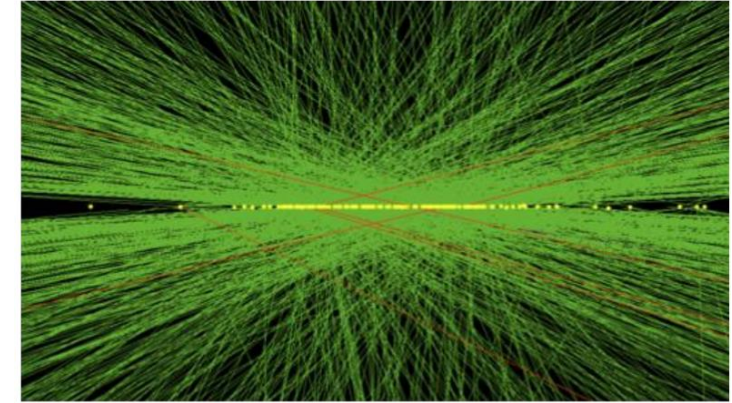
Leena Diehl, Marc Hauser, Karl Jakobs, Montague King, Gregor Kramberger, Ulrich Parzefall, Dennis Sperlich

30.06.2022

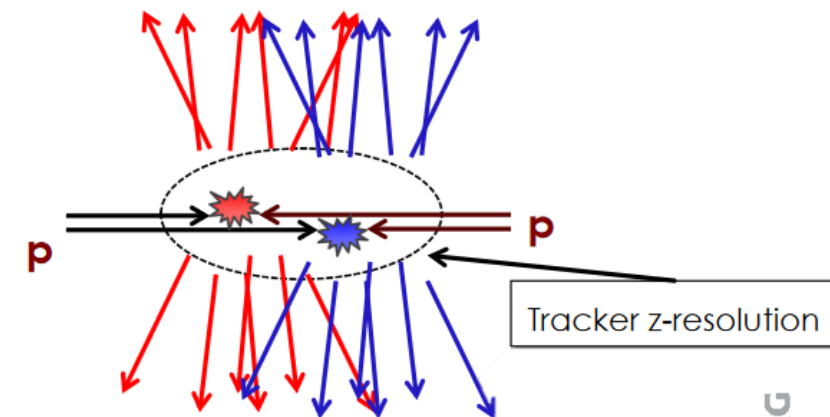


# Introduction

- Future hadron colliders challenge the tracking and reconstruction with high rates and huge pile-up
- ATLAS and CMS already aim for 30-40ps timing resolution, future trackers like for FCC will demand timing of 5ps while still providing position resolution below 10  $\mu\text{m}$  in high density environments
- High radiation doses challenge the sensors additionally
- Silicon sensors are proven to be very radiation hard and have a short charge collection time – current and future choice for tracking detectors
- Many collaborations working on improving time resolution, e.g.
  - Ultra Fast Silicon Detectors (UFSDs - LGADs)
  - 3D pixel sensors dedicated for timing

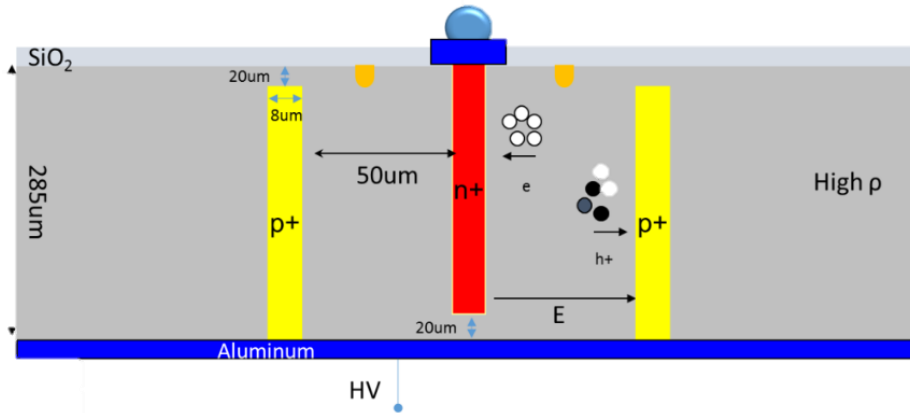


Tracking z-resolution larger than vertex-separation: Ambiguous Track-to-vertex association



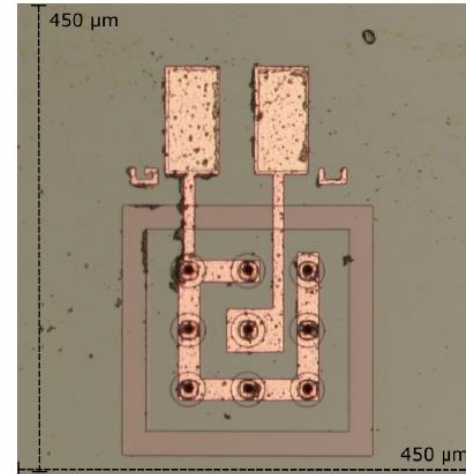
N. Cartiglia, INFN, Hiroshima Conference 2017

# 3D sensors



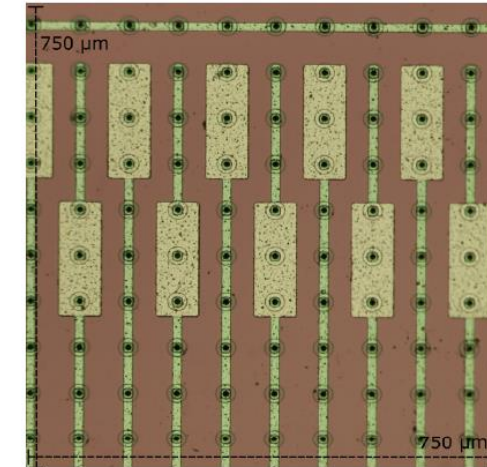
- Junction columns etched into the sensor bulk
- 235  $\mu\text{m}$  or 285  $\mu\text{m}$  active thickness
- Columns etched 215  $\mu\text{m}$  and 265  $\mu\text{m}$
- Produced by CNM Barcelona

Pixel sensor



- Pixels: 50 × 50  $\mu\text{m}^2$  unit cell size
- Total pixel size: 100 × 100  $\mu\text{m}^2$
- 16 pixels per test structure

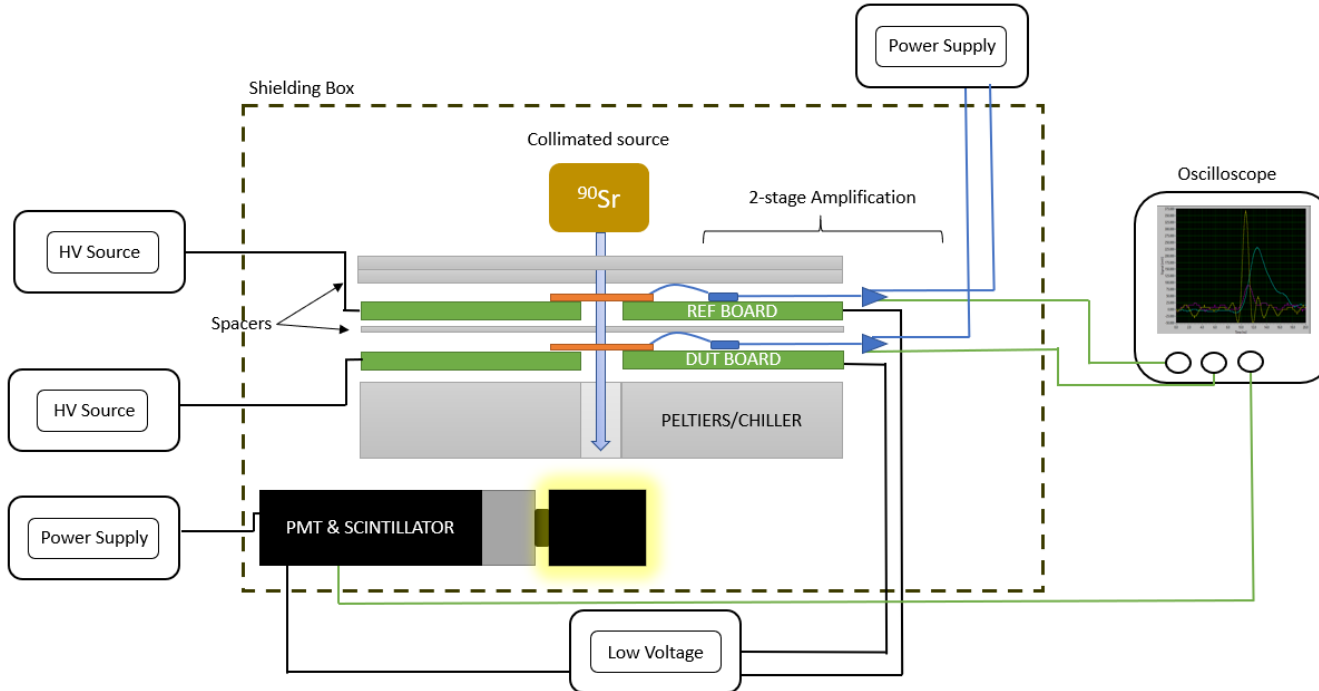
Strip sensor



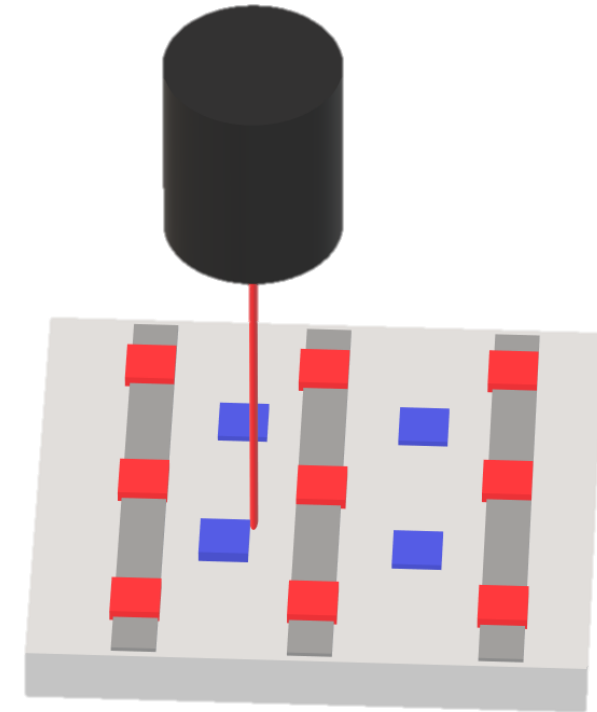
- Strips: 80 × 80  $\mu\text{m}^2$  unit cell size
- Total sensor size: 10 × 10  $\text{mm}^2$

# Experimental Setups

- Single pulses recorded of both reference and tested sensor
- About 3000 events with DUT signature for appropriate statistics
- If possible, only external triggers



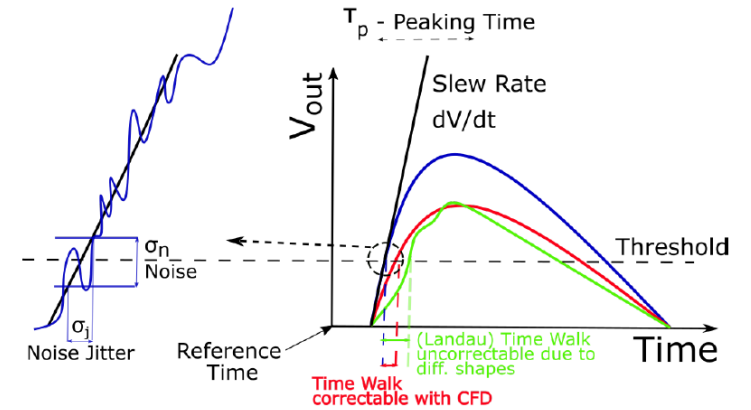
- $^{90}\text{Sr}$ -source
- LGAD reference,  $\sigma_{Ref} = 25.18 \pm 0.35 \text{ ps}$
- PMT yes/no trigger



- Top-TCT, infrared laser (1060nm)
- 2 pulses recorded (fiber splitter)
- Intensity tunable

# Time Resolution - Analysis

- Time resolution is determined using a Constant Fraction Discrimination (CFD, usually 30%)
- Full rise time is calculated (max. amplitude /slope), mean of distribution = rise time of sensor
- Jitter: Sigma of a Gauss fit to the distribution of the noise divided by the slope -  $\sigma_j = N / (\frac{dV}{dt}) \sim t_p / (\frac{S}{N})$
- Note: The measured timing characteristics are setup-dependent
  - Readout electronics and noise level influence timing
  - Results within this (or an equivalent) setup are comparable
  - However, giving a good estimation for real-life use

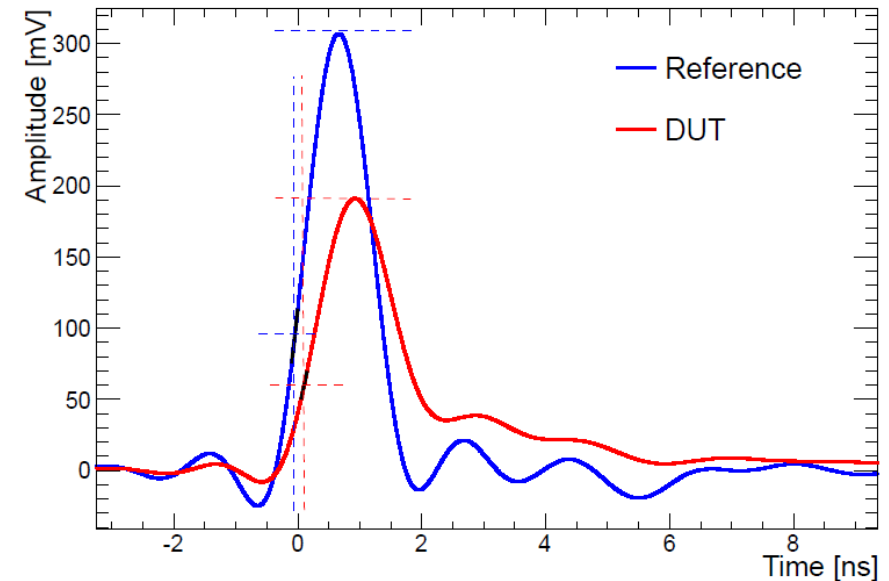


Beta Set-Up:

$$\sigma_{DUT} = \sqrt{\sigma_{TS}^2 - \sigma_{Ref}^2}$$

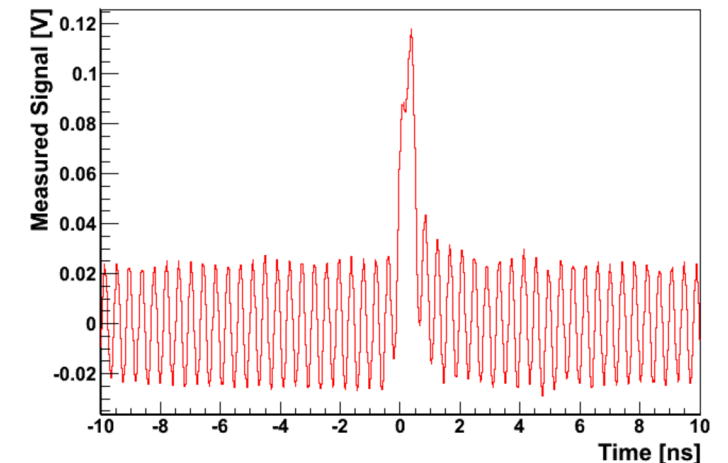
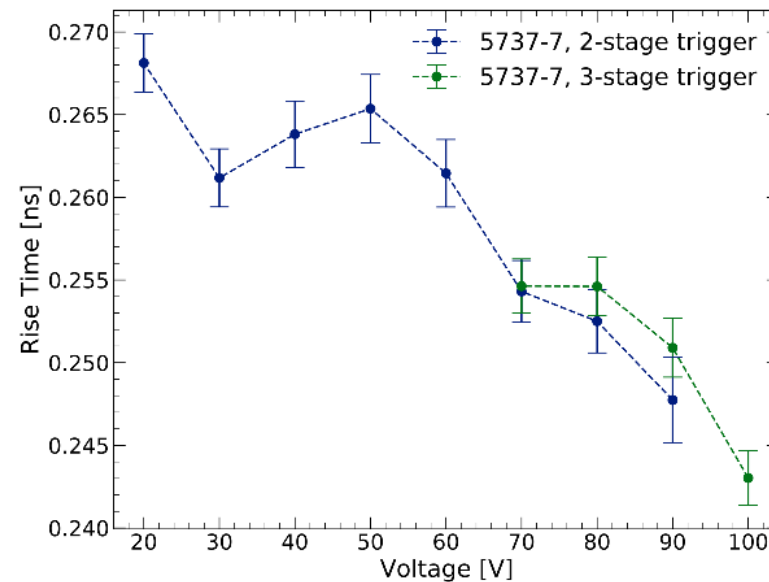
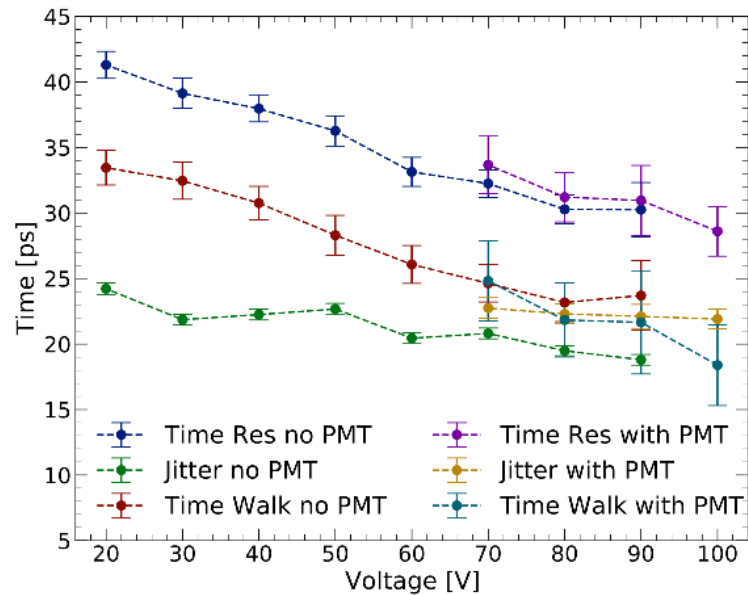
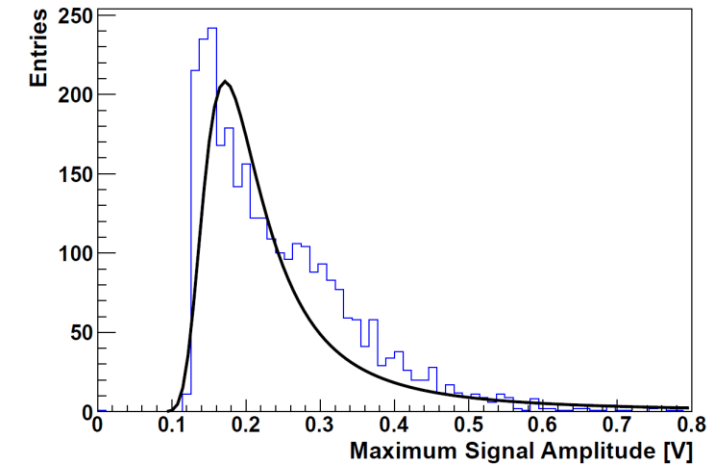
TCT Set-Up:

$$\sigma_{DUT} = \sigma_{TS} / \sqrt{2}$$



# Time Resolution: 3D Pixel sensors

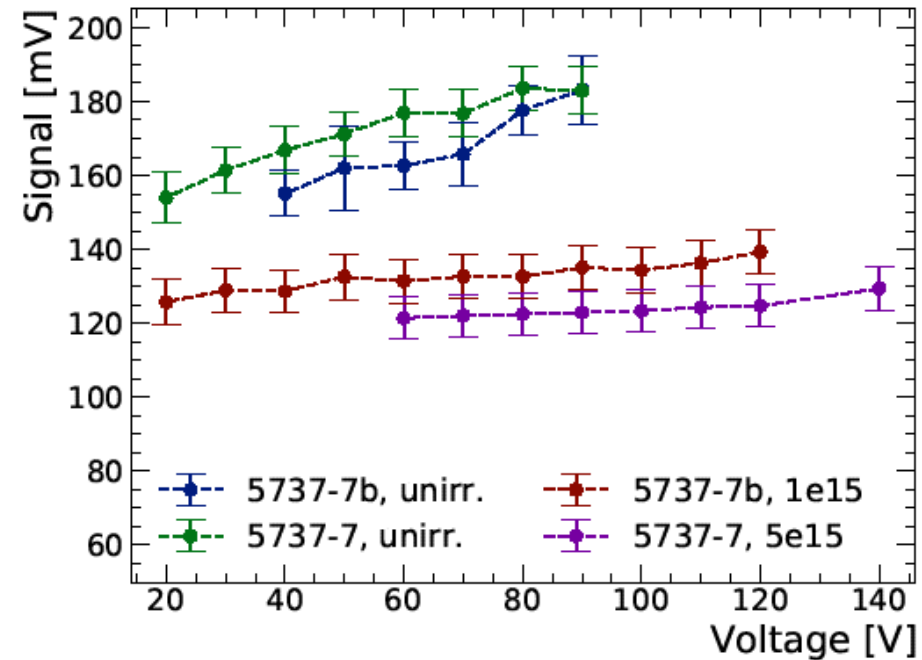
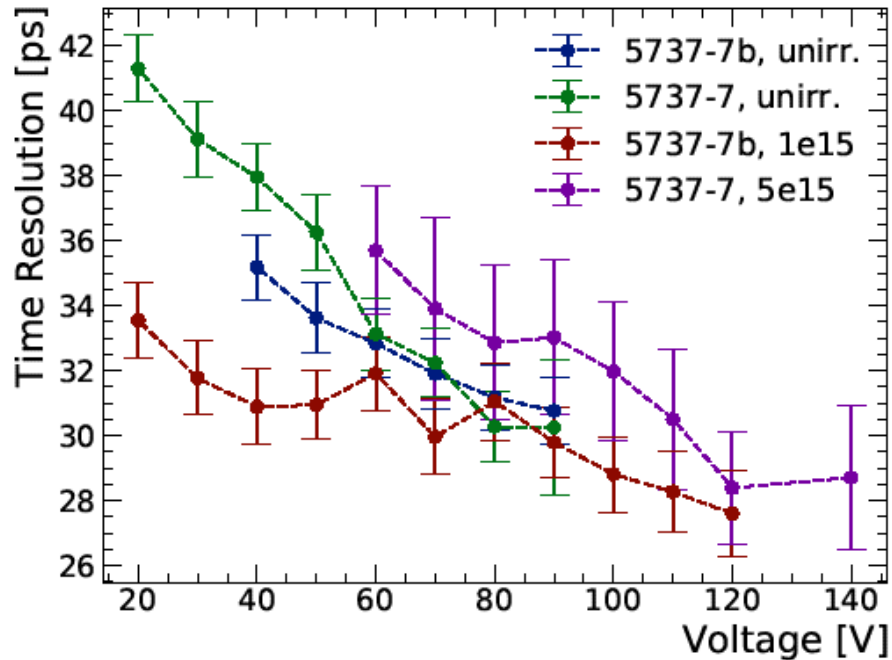
- Sanity Check: Comparison with/without additional PMT trigger
  - With PMT: Very low rate – pick-up noise problems
  - Without PMT: overestimation of MPV
  - Otherwise: Very comparable results
- All further measurements without PMT – improved statistics and measurement time, while time resolution characteristics are maintained



Average waveform with PMT trigger

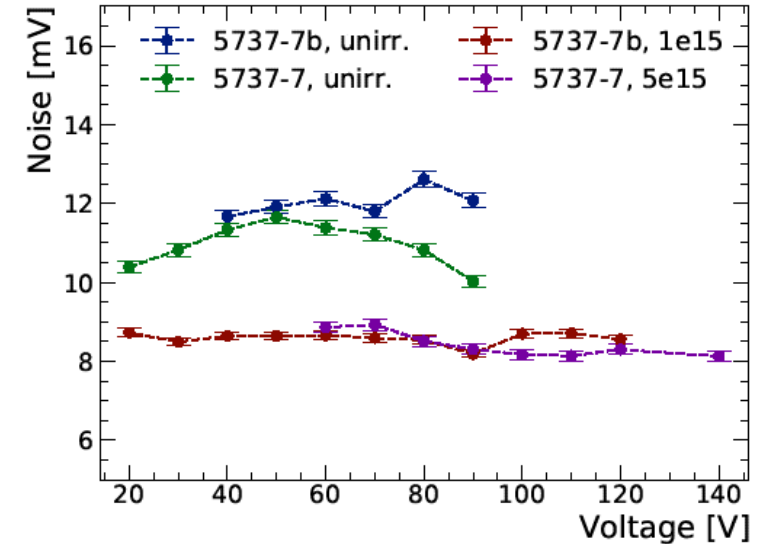
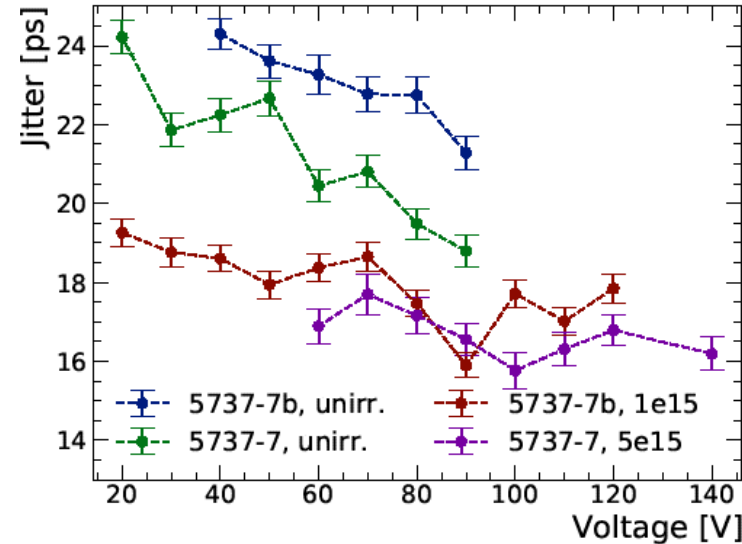
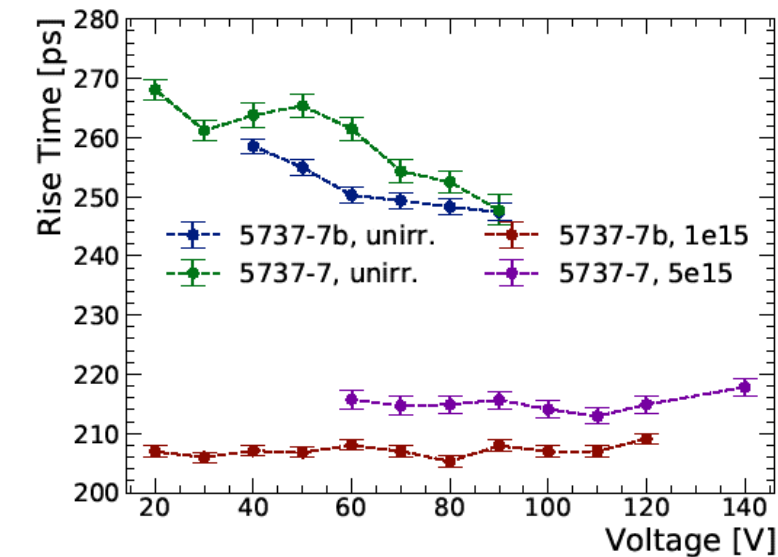
# Time Resolution: 3D Pixel Sensors

- Before irradiation, sensors reach about 30-31 ps time resolution at room temperature
- After irradiation the sensors reach 28 ps at  $-18^{\circ}\text{C}$ , but are consistent with unirradiated
- Signal decrease with irradiation



# Time Resolution: 3D Pixel Sensors

- Rise time significantly lower for 1e15 and 5e15
- Jitter for irradiated sensors slightly lower (measured cold)
- Lower noise for 1e15 and 5e15 (cold measurement)
- Smaller voltage dependence for rise time and jitter of the irradiated sensors

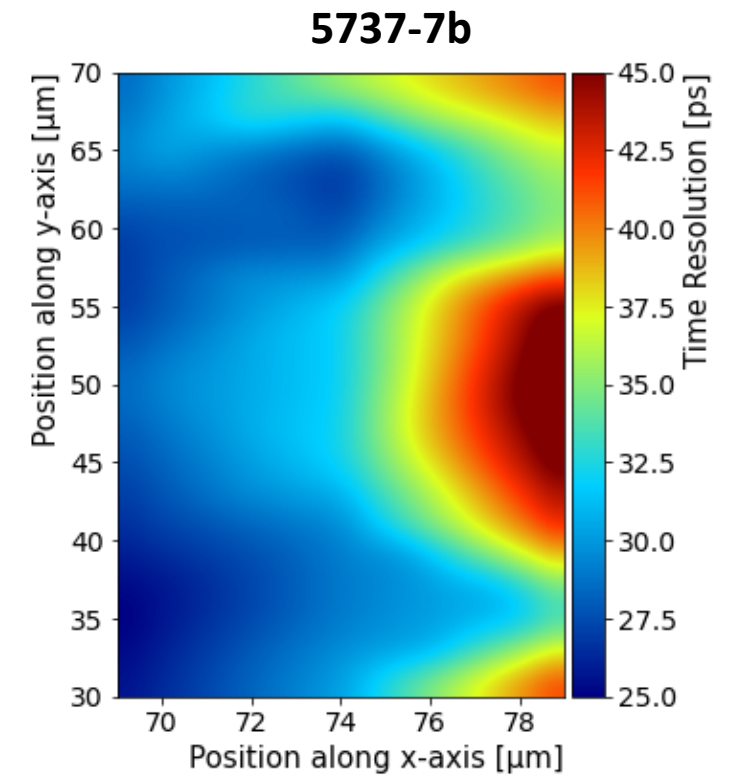
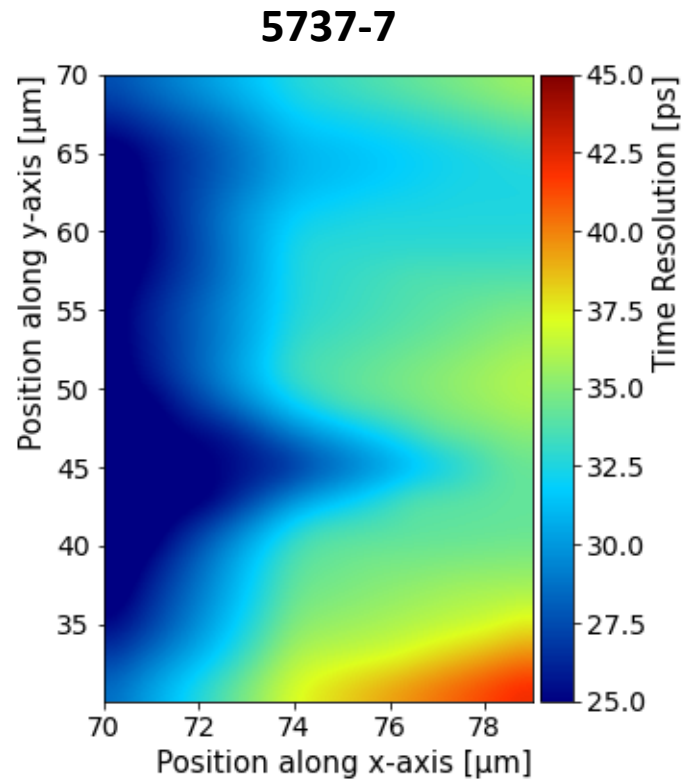
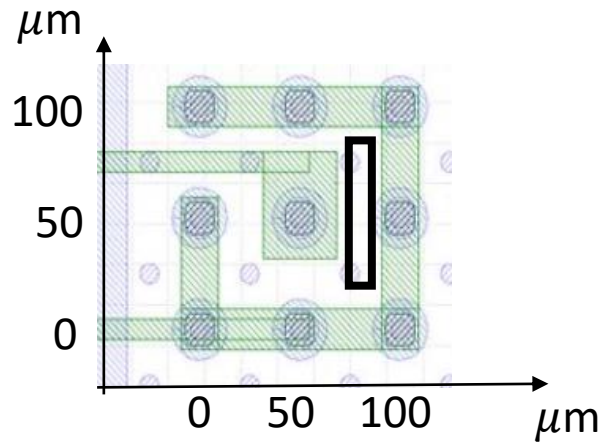




# Time Resolution: Unirradiated 3D Pixel Sensors

- Time resolution measured at 60 V for a  $10 \times 40 \mu\text{m}$  area in  $5 \mu\text{m}$  steps and interpolated
- Both sensors: Similar cell structure recognizable :
  - Better resolution closer to the readout column
  - Worse resolution closer to the other junction columns
  - Range from 23-43 ps/ 25-47 ps

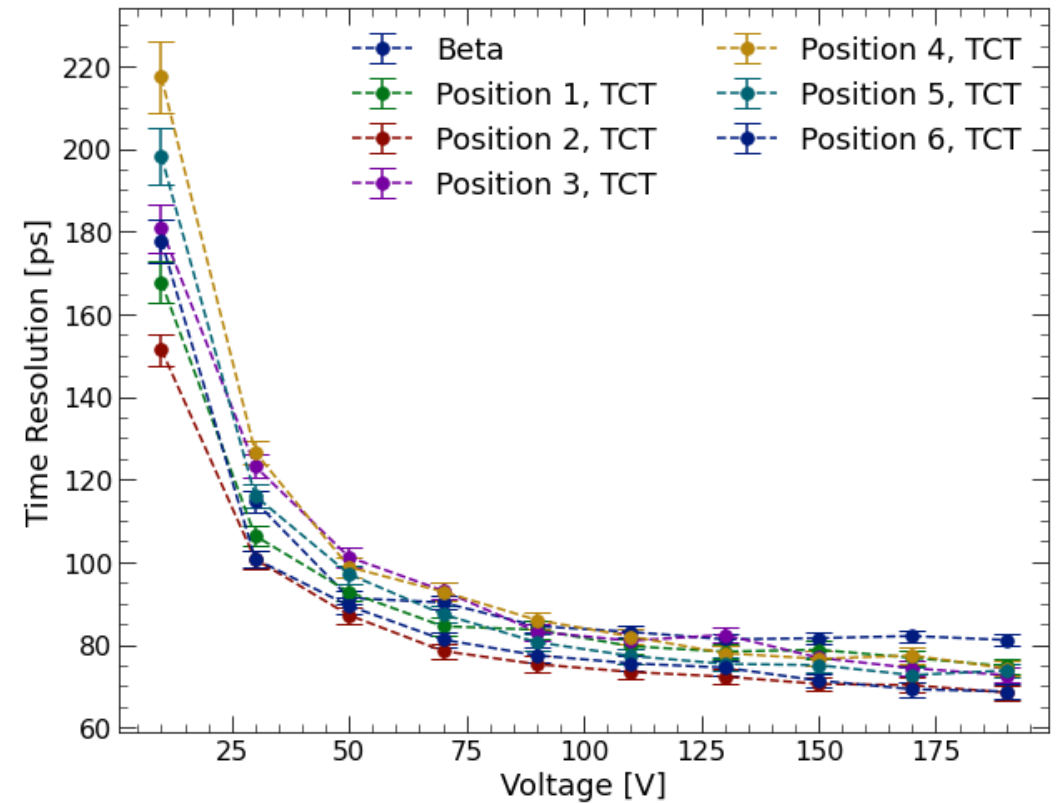
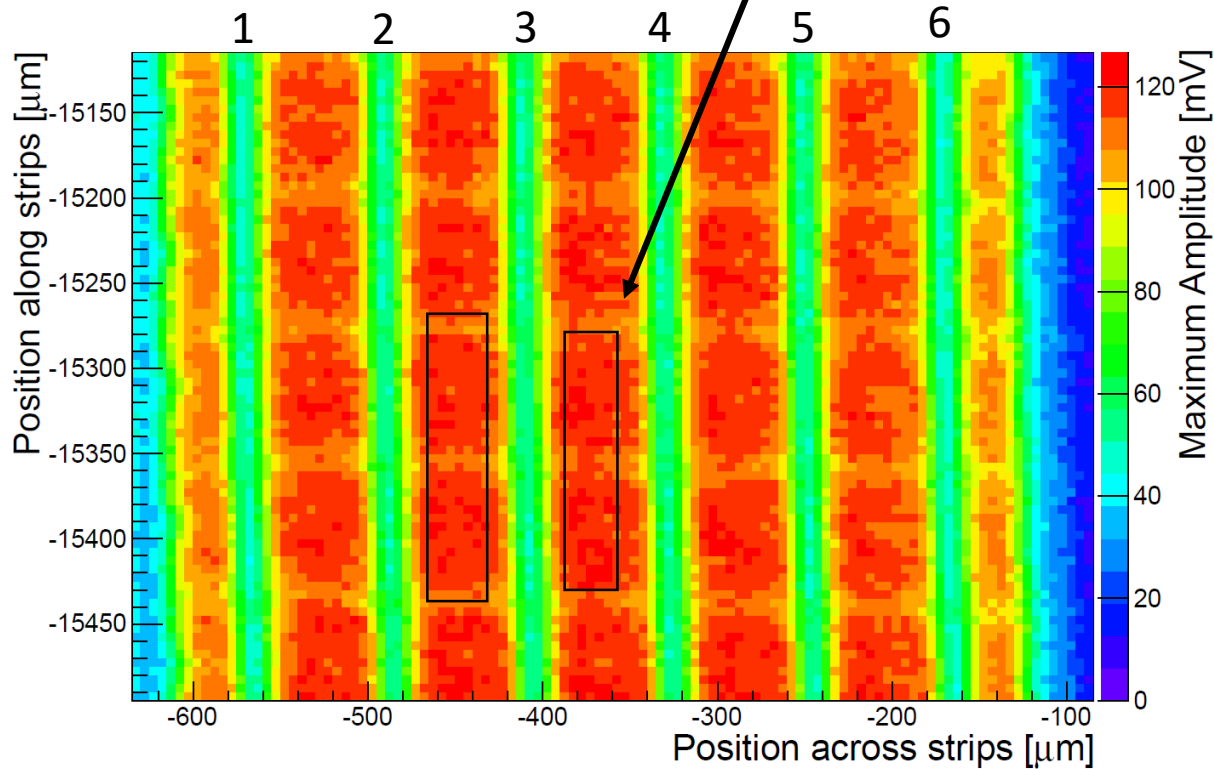
- Differences: Uncertainties in position, laser focus, laser intensity



# Time Resolution: 3D Strip Sensor

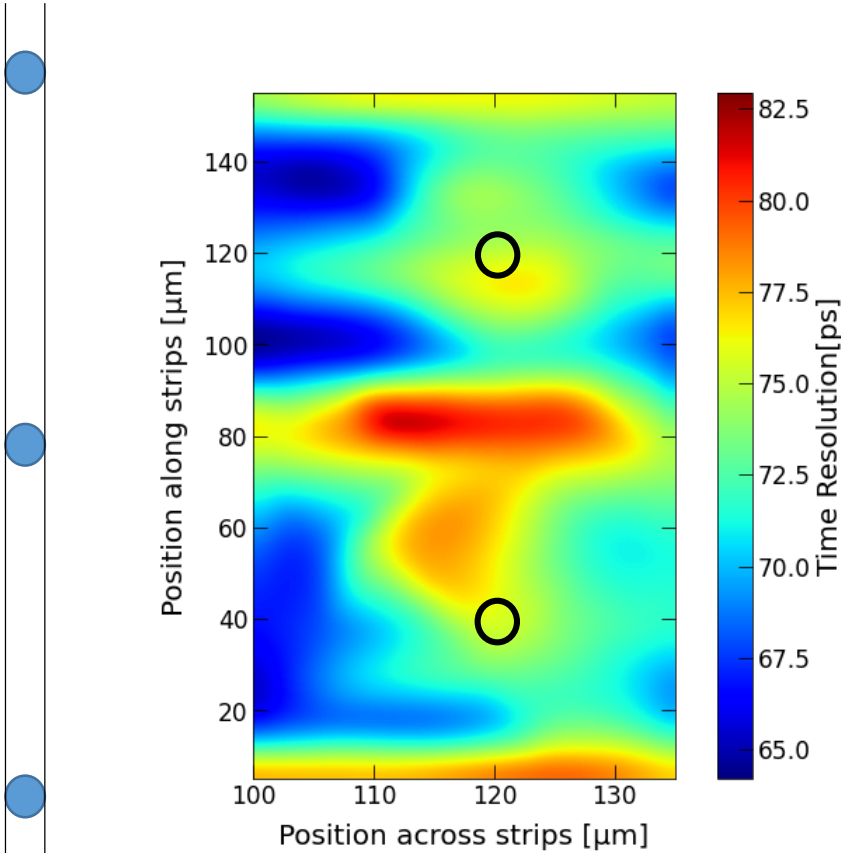
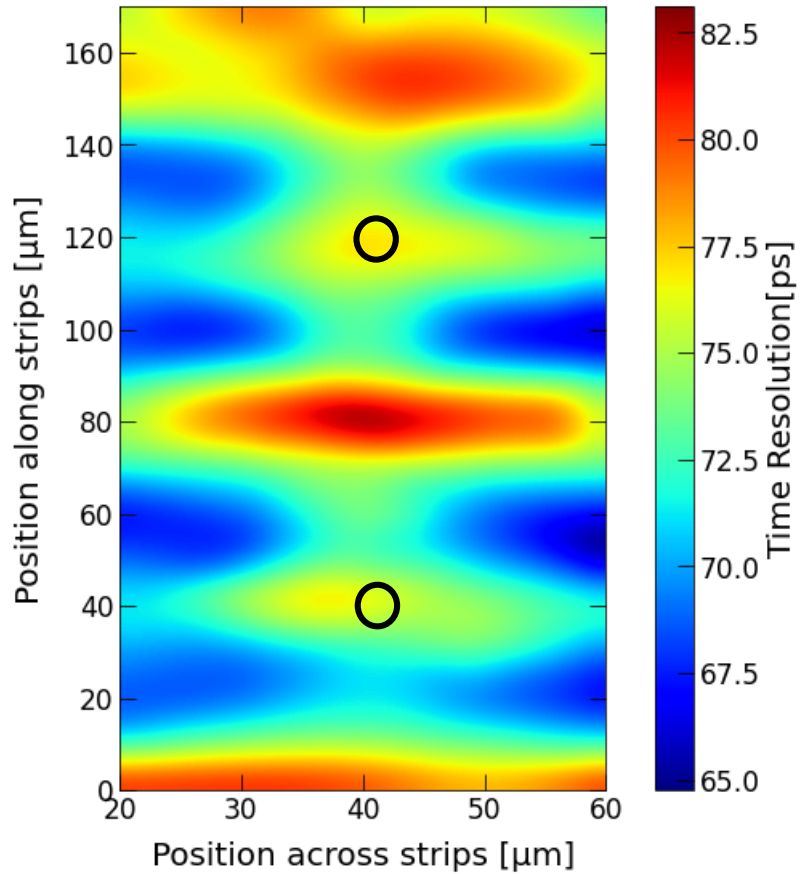
- 3D strip sensor: 235  $\mu\text{m}$  thickness,  $80 \times 80 \mu\text{m}^2$  cell size, 6 channels connected to readout
- Measured with TCT and Timing Set-Up
- For high voltages: Time resolution of about 75 ps reached

Measured areas for TCT-Timing



# Time Resolution: 3D Strip Sensor

Position dependent measurement of the time resolution with the TCT, measured at 150 V



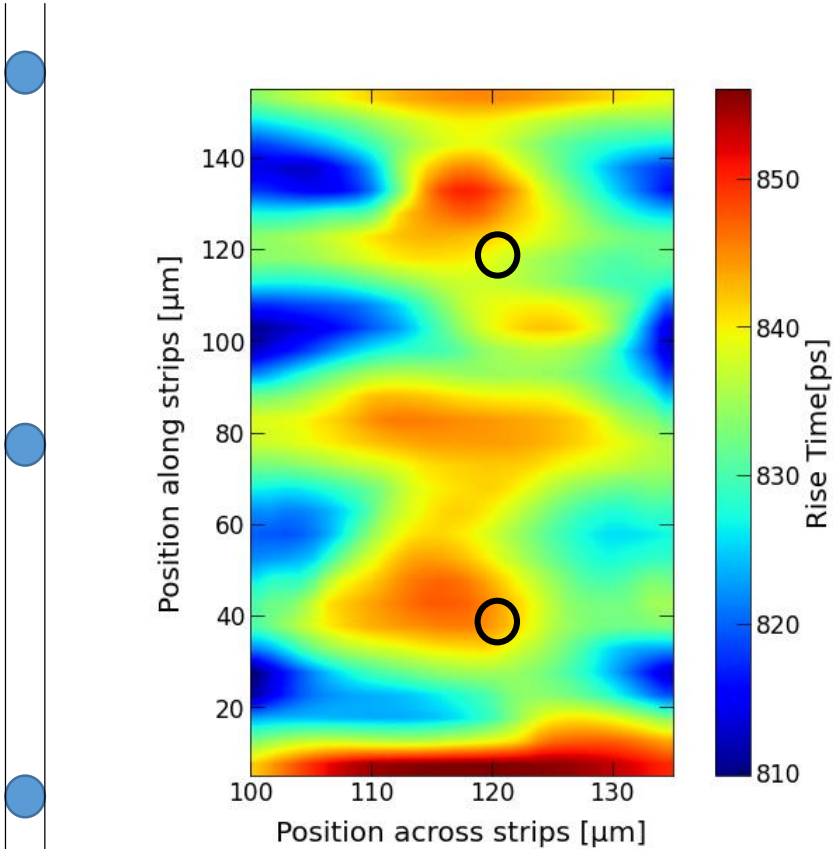
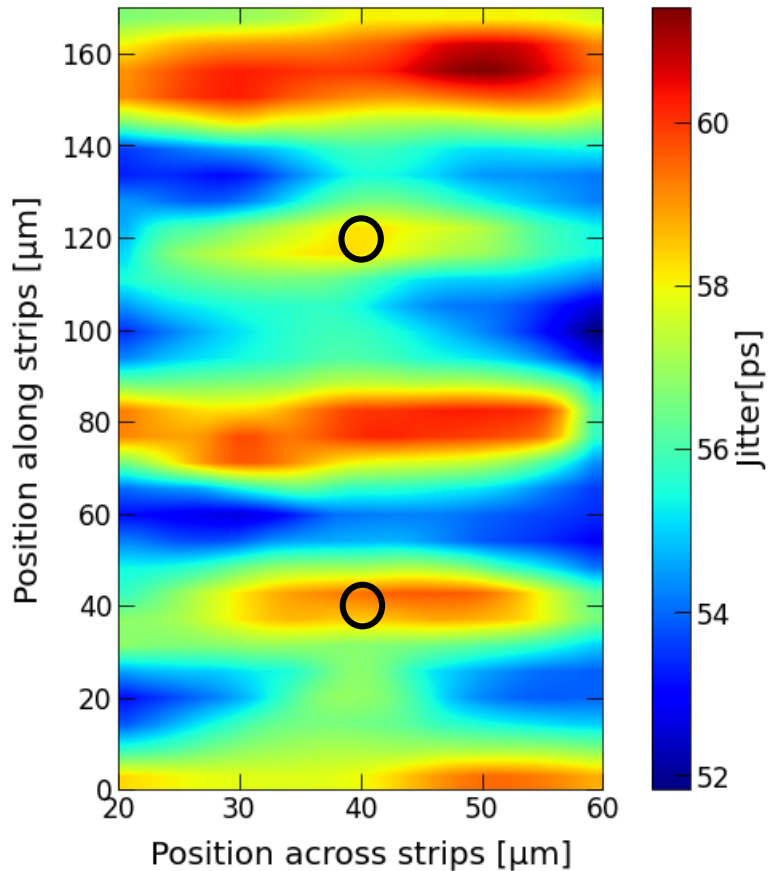
- Clear cell structure
- Worse resolution ● between junction columns
- Worse resolution around ohmic columns ○
- Resolution correlates to the expected el. Field
- Resolution between 65 and 83 ps

2

3

4

# Time Resolution: 3D Strip Sensor



- Clear cell structure
- Similar patterns for jitter and rise time
- Both correlate to the expected el. Field
- Rise Time between 810 and 855 ps
- Jitter higher than in Beta Set-Up, 52-62 ps

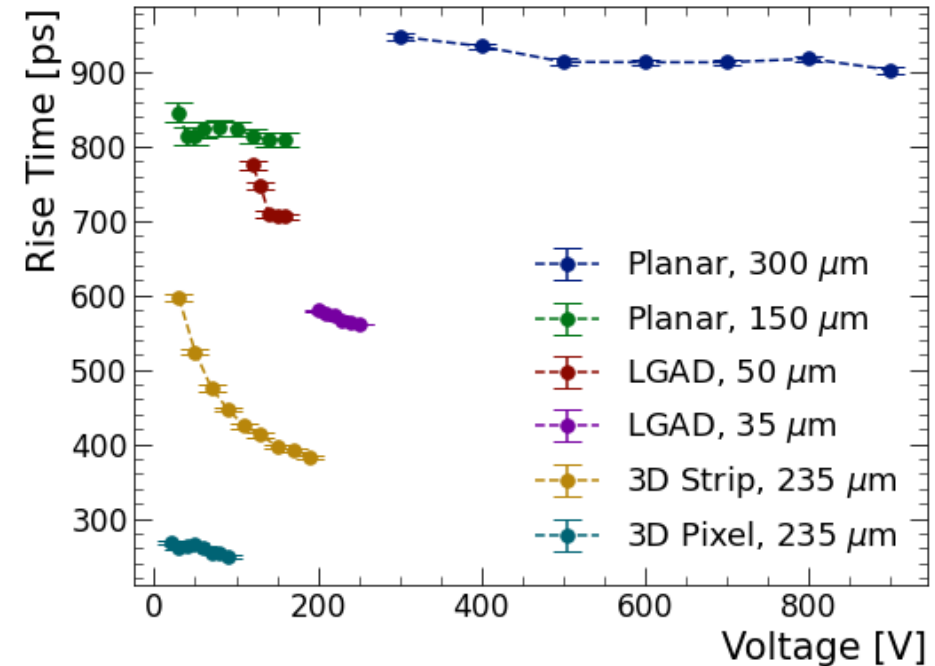
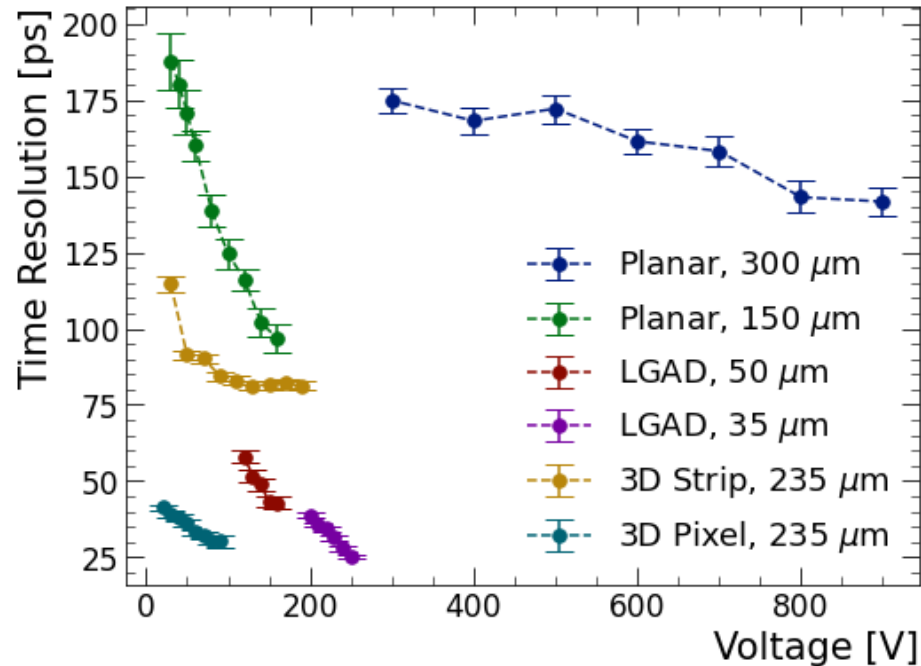
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# Comparison – 3D vs other designs

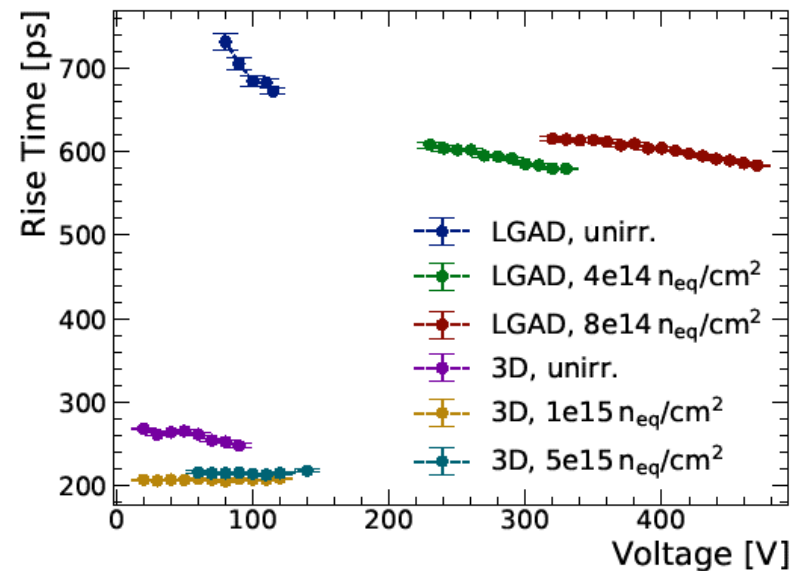
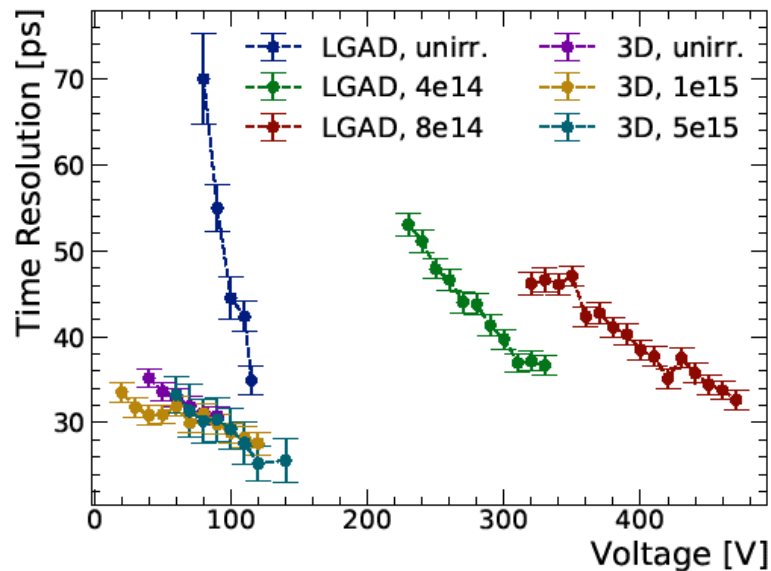
- Planar: Strips sensors -  $300\mu\text{m}$  thickness (ATLAS, Hamamatsu) and  $150\mu\text{m}$  thickness (CMOS, LFoundry)
- LGADs – Pad diodes:  $50\mu\text{m}$  thickness, high gain layer doping and  $35\mu\text{m}$  thickness, lower gain layer doping
- 3D Sensors: Strip Sensor and Pixel Sensor -  $235\mu\text{m}$  thickness



- 3D Sensors have the overall fastest rise times, especially the pixels – significantly shorter than LGADs
- As expected, 3D strip sensors show better time resolutions than planar strip sensors, but only pixel sensors are competitive with LGADs
- Benefit: Lower voltage necessary for 3Ds than for LGADs

# Comparison – LGAD vs 3D Pixel

- Compared LGADs: 50  $\mu\text{m}$ , high gain layer doping (HPK run 2)
- LGADs need significant voltage increase to reach same time resolution (gain layer degradation)
- Improved time resolution for 3D pixels after irradiation – at the same voltage
- Significantly lower rise time – improving after irradiation for both LGADs and 3Ds
- Note: This are not the latest/ fastest generation of LGADs – but the 3D sensors prove to be competitive





# Conclusion and Outlook

- Time resolution of silicon sensors is an important research area for upcoming and future colliders
- 3D sensors reach a time resolution competitive with LGADs (around 30 ps)
- 3D pixel sensors slightly improve resolution after irradiation to  $5 \times 10^{15} n_{eq}/cm^2$  while the bias voltage range stays the same (up to 28 ps are reached)
- The position dependent time resolution measured correlates very well with the electric field distribution
- **Outlook:** Test of higher irradiation doses and different 3D sensor geometries, including sensors designed specifically for timing purposes (dedicated 3D timing project)



# Thank you for your attention!

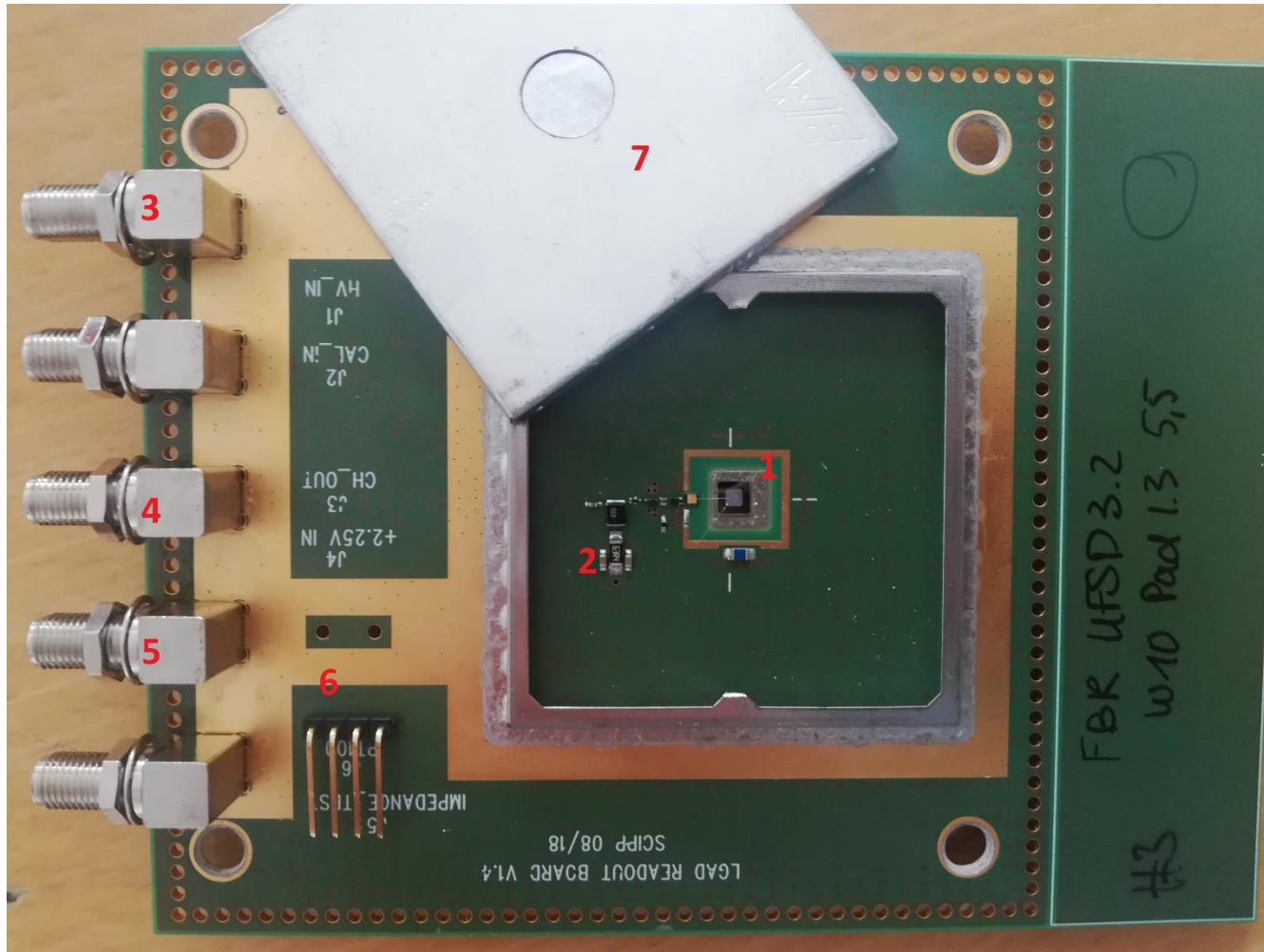
*Acknowledgments: Big thanks to Gregor Kramberger, Alissa Howard, Giulio Pelligrini, Dario di Simone, Oscar Ferrer, Neil Moffat, Pablo Fernandez-Martinez, Sebastian Grinstein, Christopher Betancourt for the collaboration, help and support.*



# BACKUP



# LGAD Readout Board



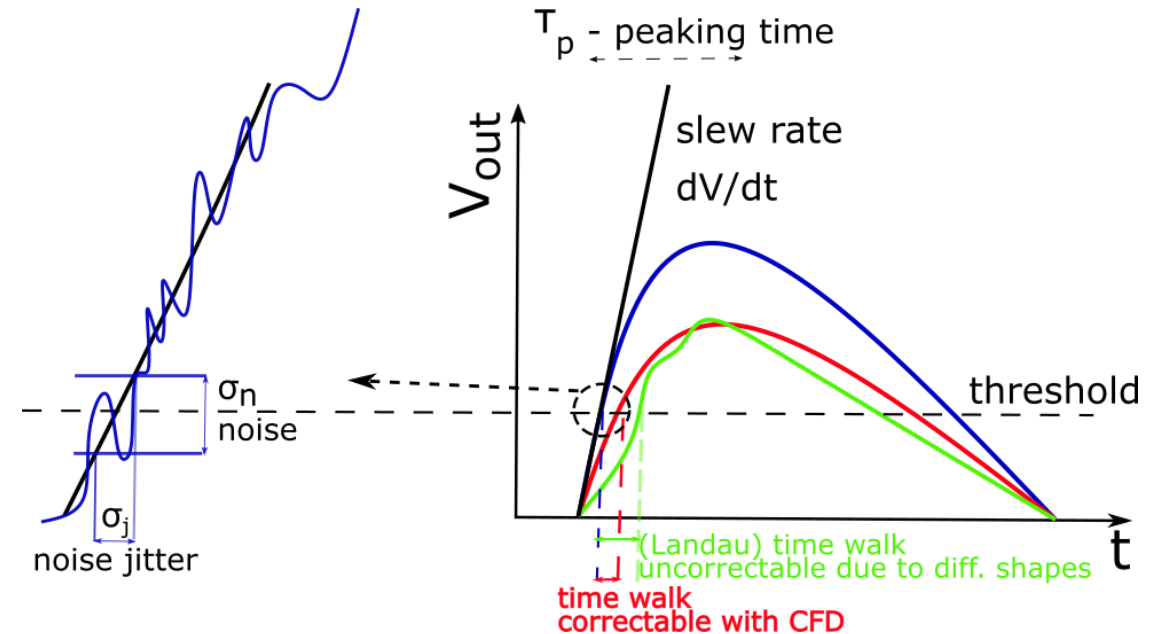
1. Bonded LGAD
2. Amplifier
3. High voltage connector
4. Readout connector
5. Low voltage connector
6. PT100 connector
7. Lid

# Time Resolution - Components

- Main components: Jitter and time walk:  $\sigma_t^2 = \sigma_j^2 + \sigma_{TW}^2$
- Jitter component  $\sigma_j$ : Determined by the rise time at the amplifier output  $dV/dt$  and the noise level  $\sigma_n$ :

$$\sigma_j = \frac{\sigma_n}{|dV/dt|} \approx \frac{\sigma_n}{|S/\tau_p|} = \frac{\tau_p}{S/N}$$

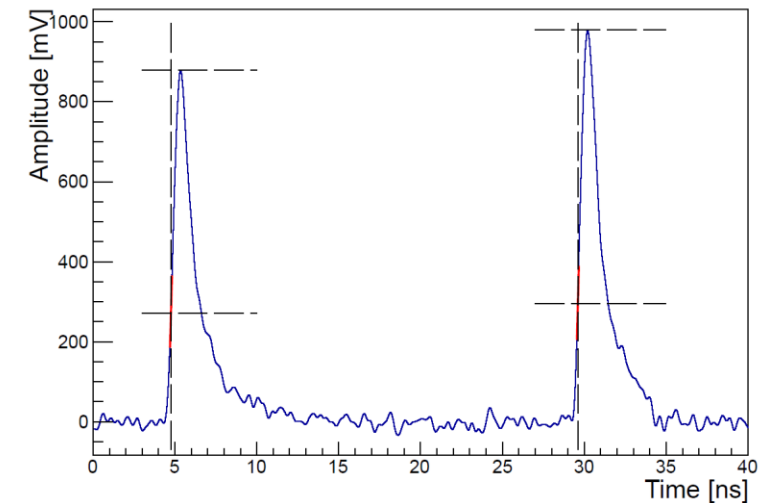
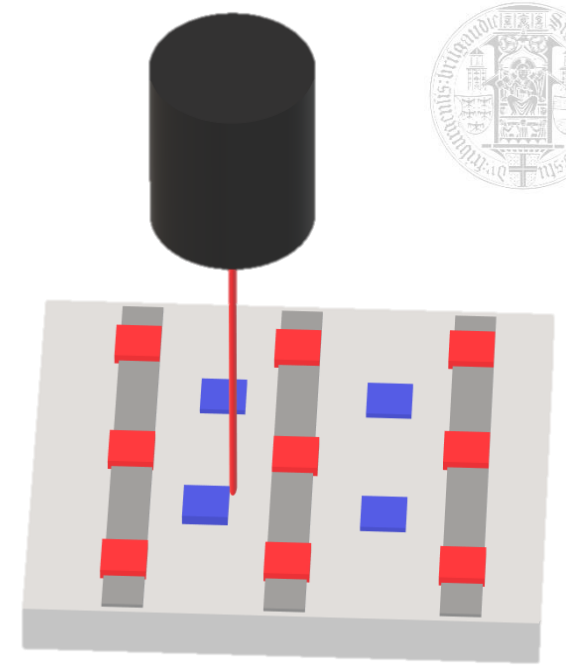
- Time walk component includes:
  - Weighting field/ el. Field contribution
  - Landau fluctuations in signal shape
  - Landau fluctuation in the amount of deposited charge (correctable)
- Time Walk component depends strongly on the sensor design



# TCT Set-Up for Timing

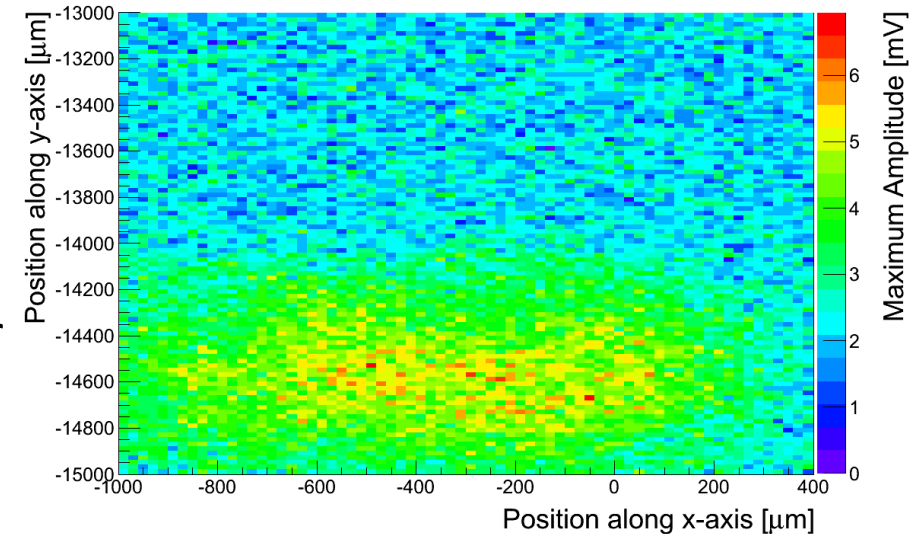


- **Transient Current Technique:** Charge created by a short laser pulse
- The current arising from the created e/h-pairs is amplified and then recorded with an oscilloscope
- **Top-TCT:** Laser on sensor surface, laser wavelength 1060 nm (infrared)
- **First:** Scanning the sensor area to determine the position of the columns
- For each specific position on the sensor: 3000 single events recorded
- Two pulses recorded per event: Using a fiber splitter and a cable (25 ns delay)



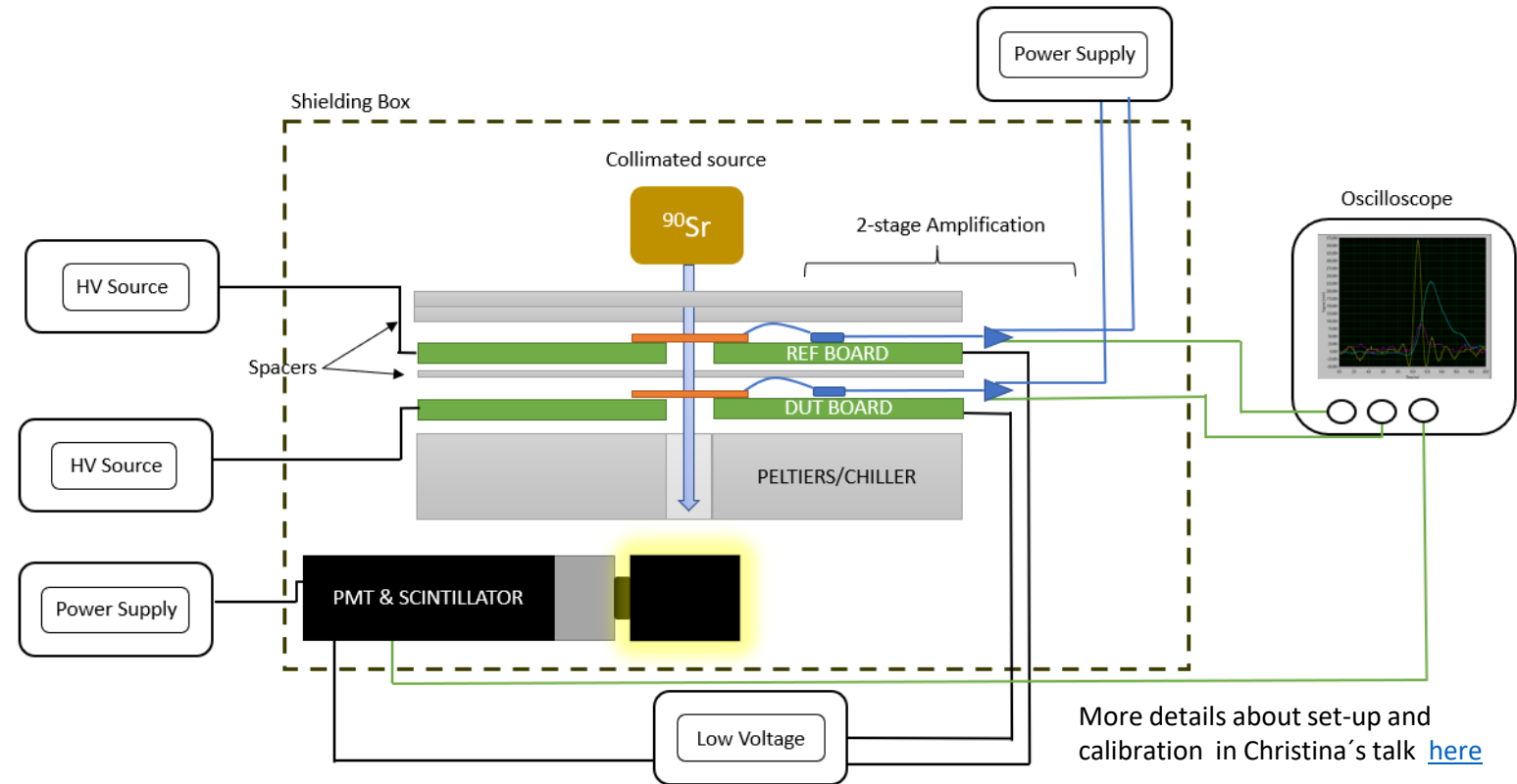
# TCT Set-Up for Timing

- Intensity regulation: **N**eutral **D**ensity **F**ilter transmitting only 25% of light
- TCT-Timing measurements have several difficulties:
  - Finding the focus on tiny devices such as the 3D pixels is tedious
  - Without focus, problematic to find the metal opening at all
  - During the timing measurements: Position insecurities, as the laser has to be moved by hand with another software for each step (automated software still in development)
  - Gaussian laser beam and reflections back into the sensor from backside decrease position resolution further
- Freiburg is one of very few institutes able to successfully perform TCT-Timing measurements - so far the only one testing 3D-sensors with it



# Beta Set-Up for Timing

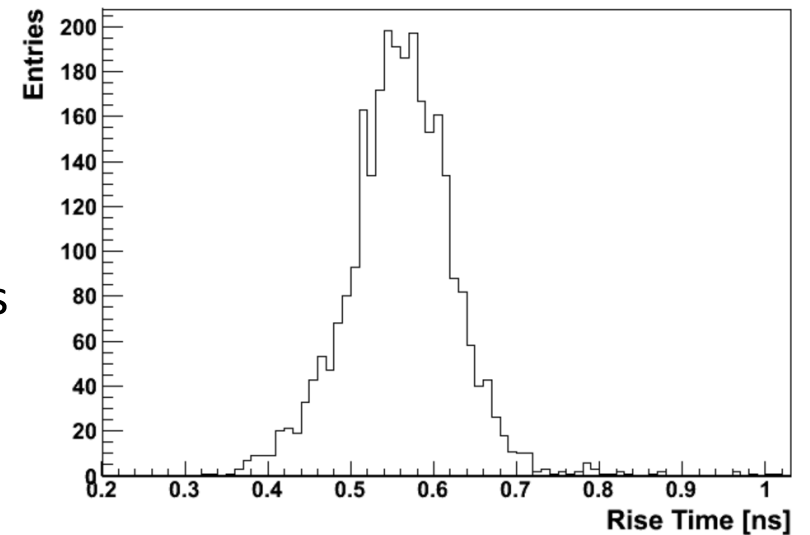
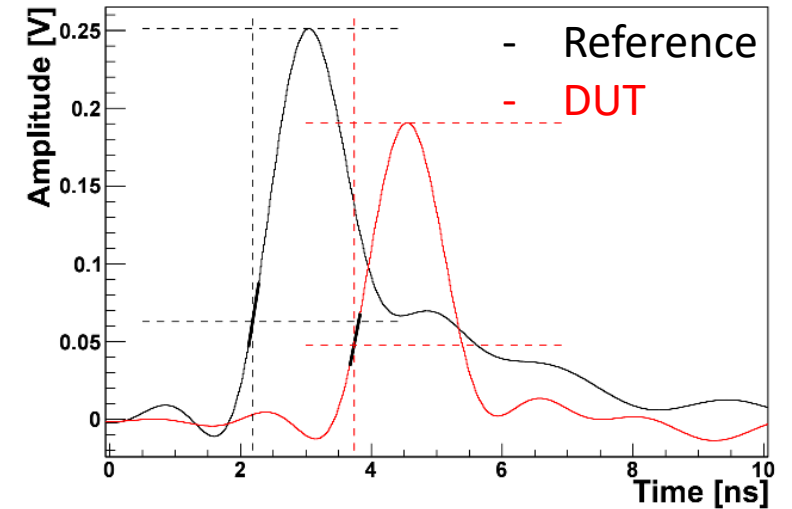
- $^{90}\text{Sr}$ -source for MIP-like electrons
- LGAD as reference sensor
- Scintillator & PMT as Yes/No trigger
- Reference and DUT signal recorded for each event



- Trigger on LGAD and PMT: 10000 events recorded, about 1/3 show a DUT signature
- Trigger on LGAD and DUT: 3000 events recorded, necessary for thicker devices or extremely small sensors

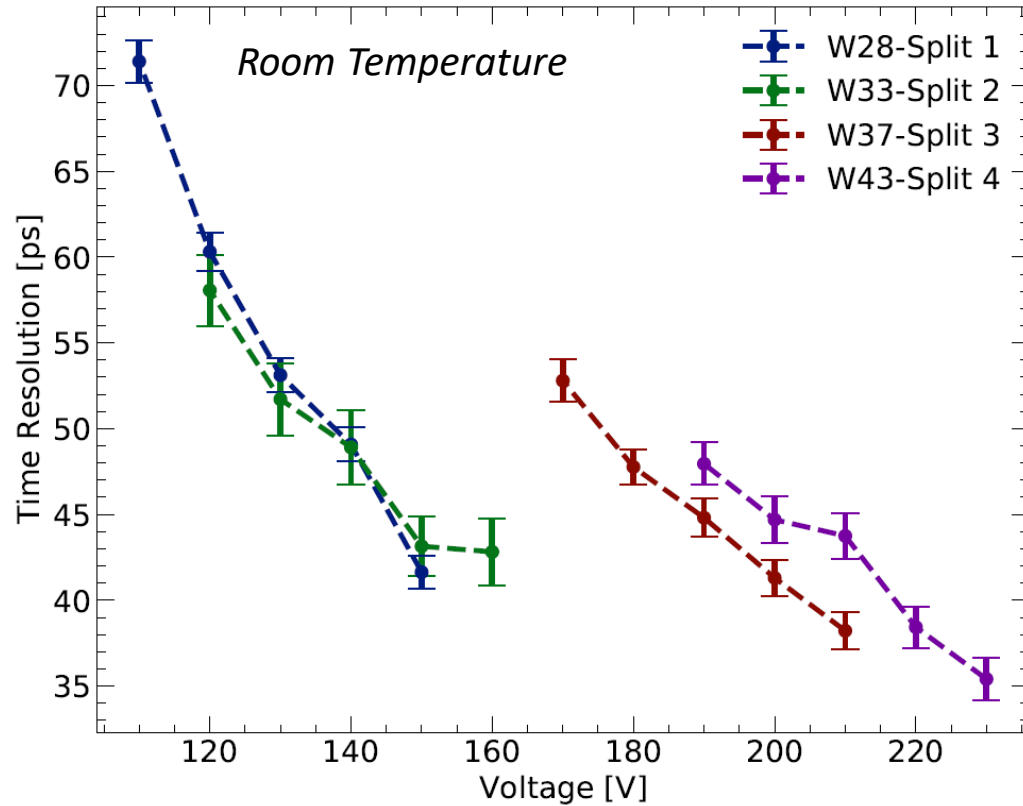
# Time Resolution: Analysis

- Maximum amplitude for each event filled into histogram – MPV of the sensor is extracted with a Landau-Gauss-Fit
- If the maximum signal is above a threshold, events used for further analysis
- **Time of Arrival** determined with **Constant Fraction Discrimination**
- Linear fit around this point to extract the slope
- Determination of the rise time for each event by dividing the maximum amplitude by the slope – mean of the distribution defines rise time

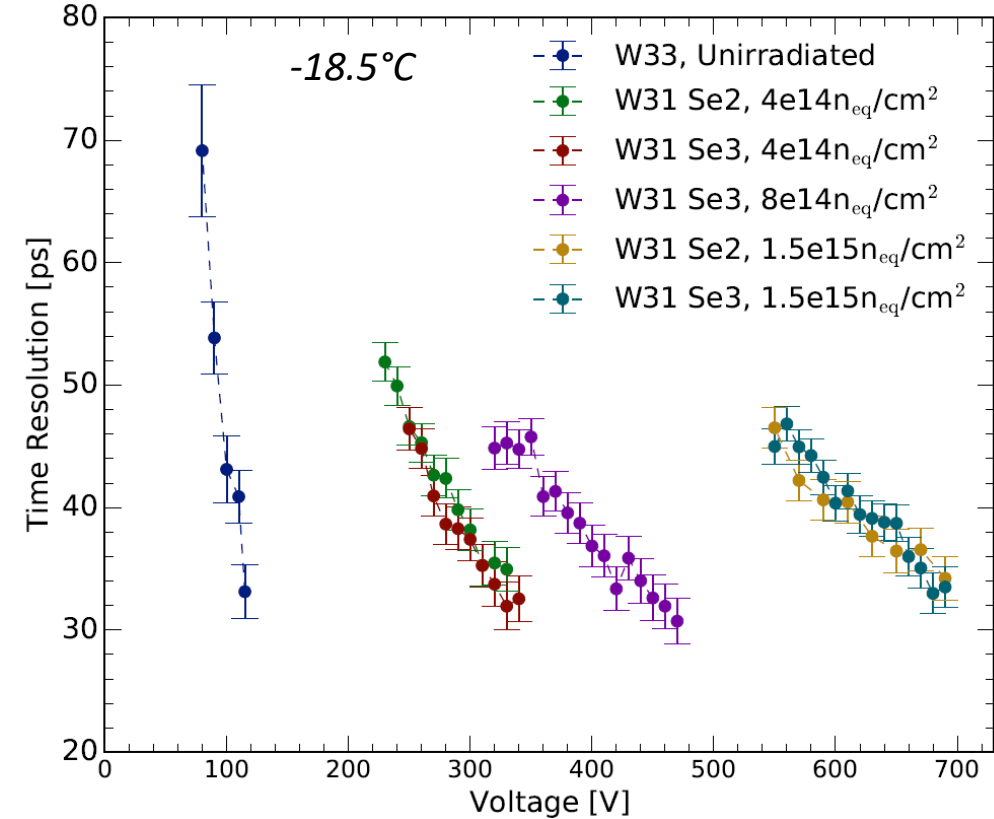


# Time Resolution: LGADs -Beta

LGADs with different gain layer doping



Irradiated LGADs from Split 2

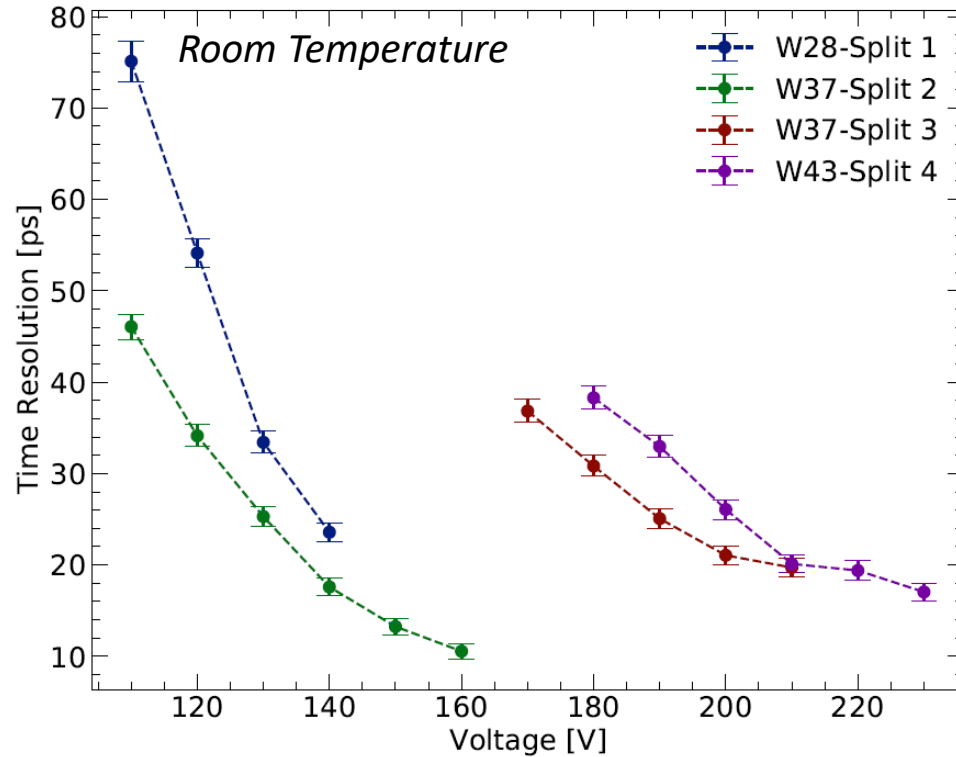


- From high (Split 1) to low (Split 4) gain layer doping – increase in voltage necessary
- Lower doping reaches in total better resolution at highest voltages
- Irradiated sensors still working, reaching approximately the same resolution as an unirradiated sensor

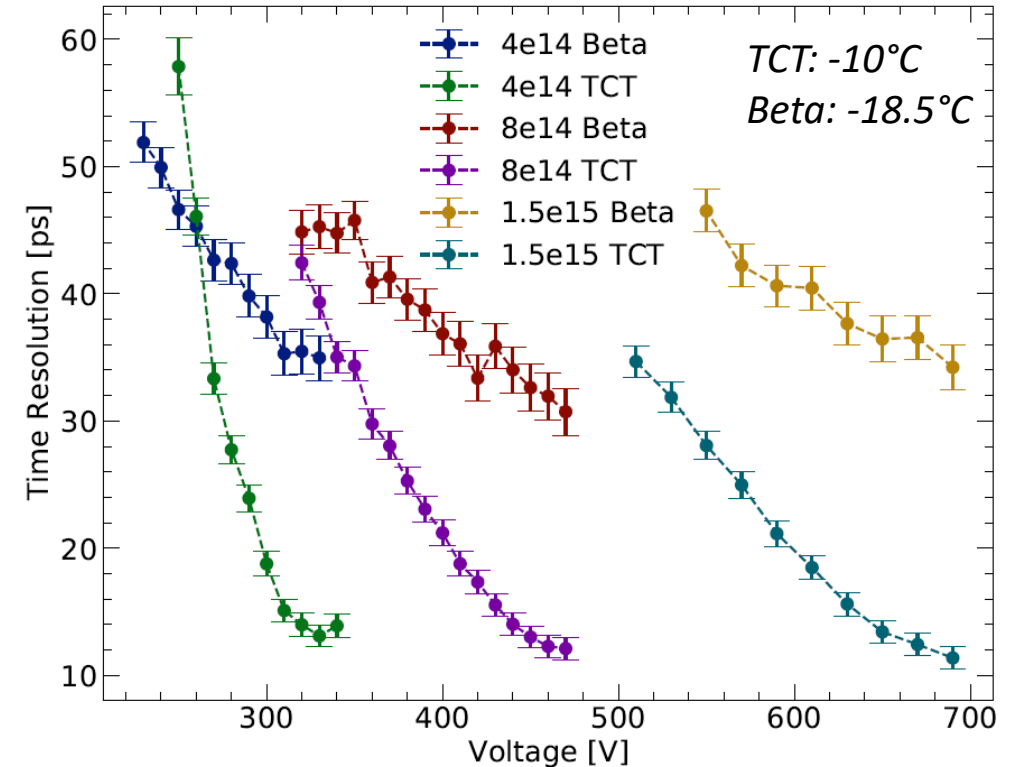


# Time Resolution: LGADs - TCT

LGADs with different gain layer doping



Irradiated LGADs from Split 2



- No Landau fluctuation in TCT setup – significantly smaller time walk contribution
- No gain layer suppression (broad laser beam): Steeper improvement of the time resolution (stronger increase in signal)

# Time Resolution: Analysis

- Noise level: Determined in a time span in the recorded waveform before the pulse
- Jitter: Sigma of a Gauss fit to the distribution of noise divided by slope
- Time Spread: Sigma of a Gauss fit to the distribution of the time difference between the two signals
- Time resolution can then be calculated

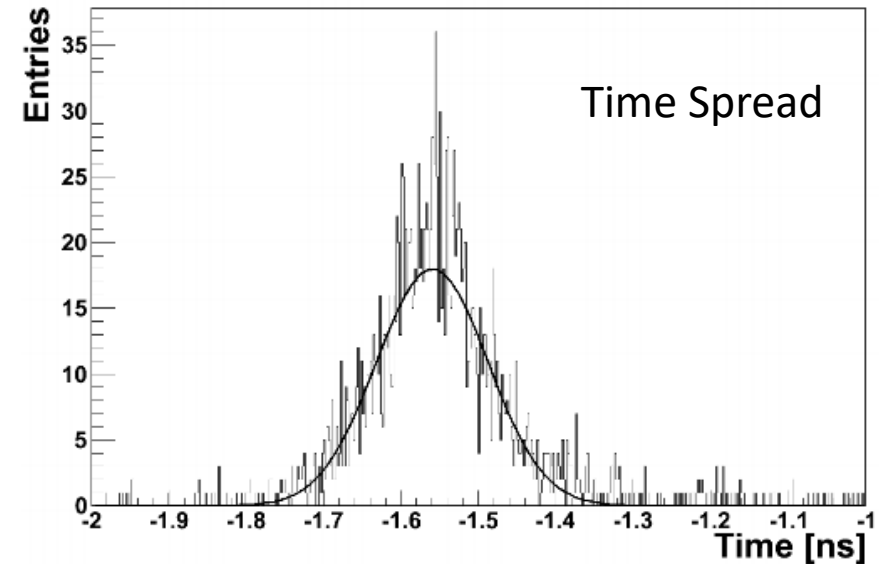
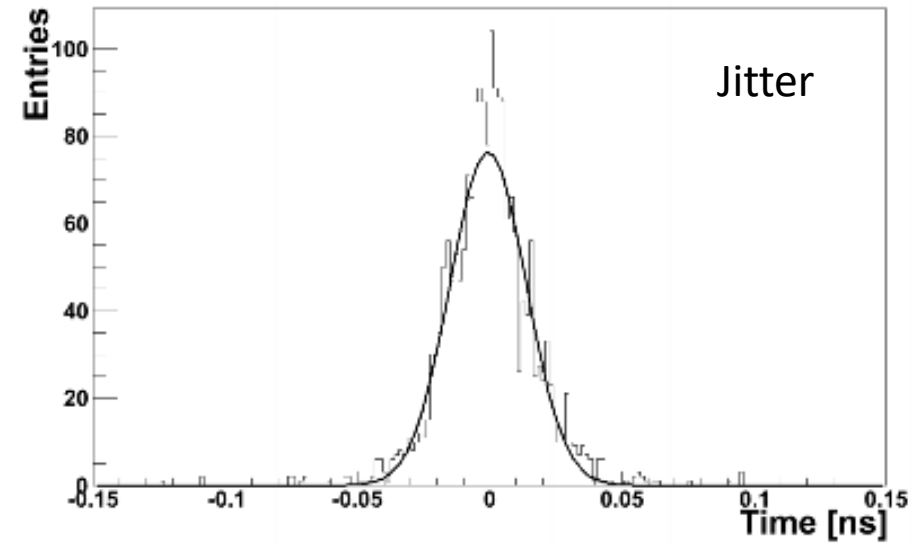
Beta Set-Up:

$$\sigma_{DUT} = \sqrt{\sigma_{TS}^2 - \sigma_{Ref}^2}$$

TCT Set-Up:

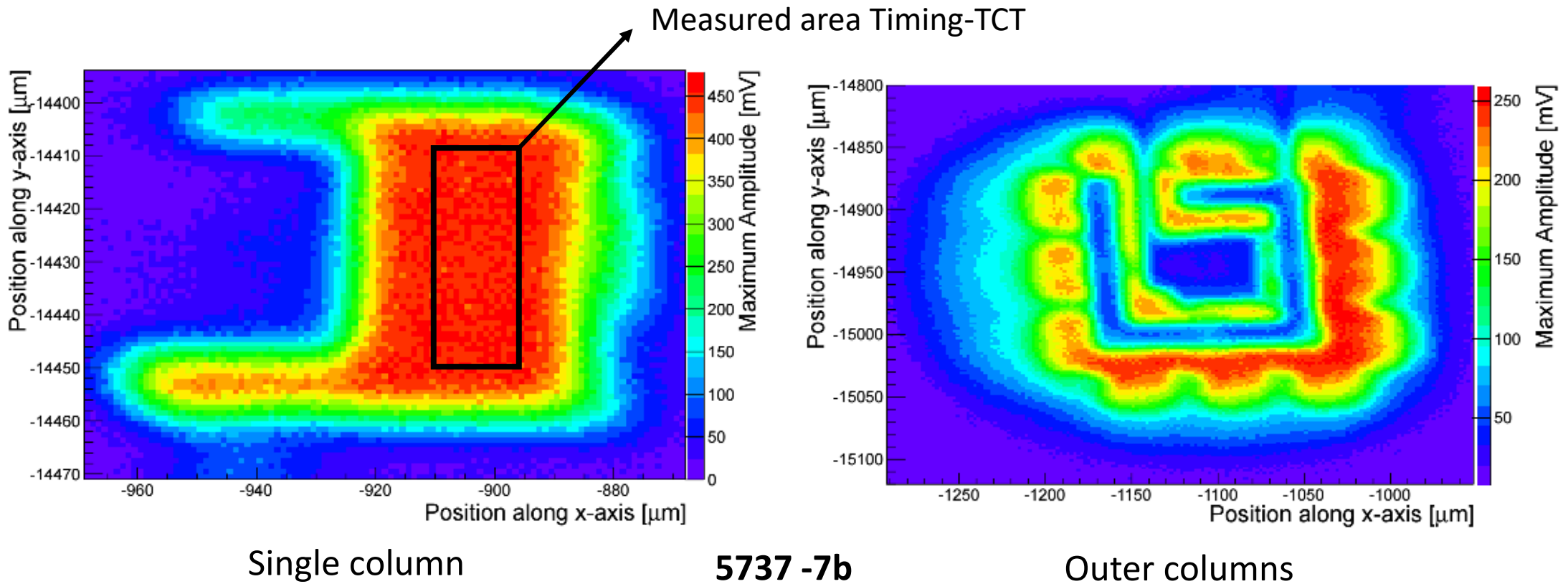
$$\sigma_{DUT} = \sigma_{TS} / \sqrt{2}$$

$$\sigma_{Ref} = 25.18 \pm 0.35 \text{ ps}$$



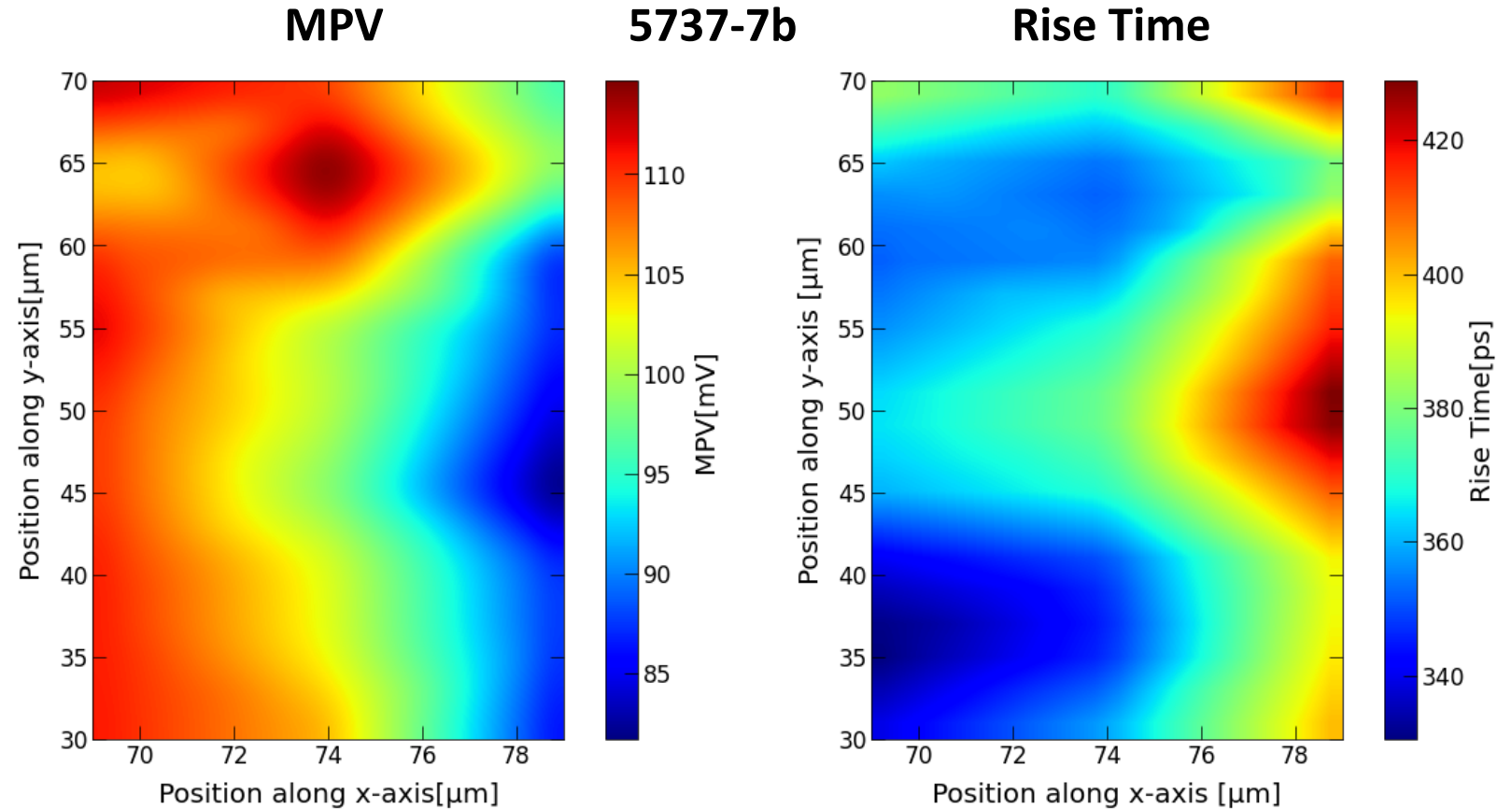
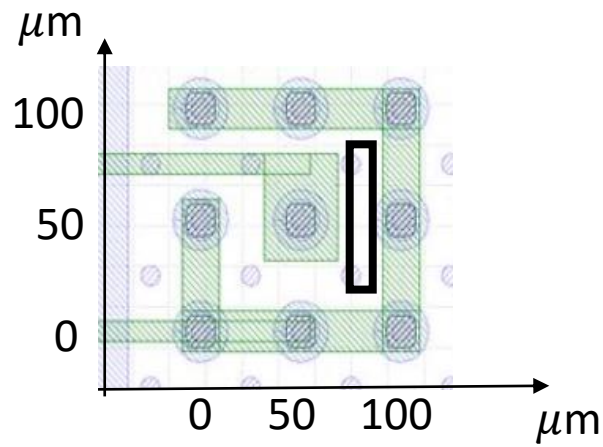
# Time Resolution: 3D Pixel Sensors

- TCT scans show very small measurable area for Timing-TCT
- Outer columns connected – indefinite electric field outside the cell explains the higher time resolution
- For Timing-TCT: Measured with laser intensity similar to one MIP-equivalent

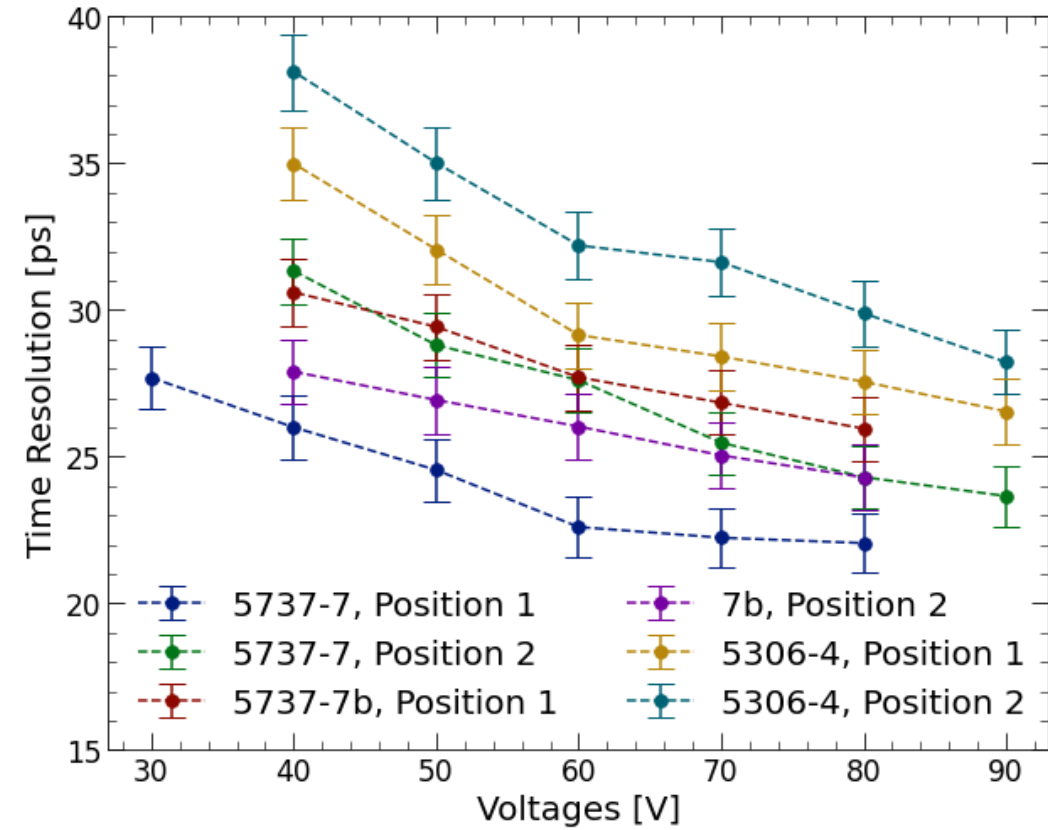
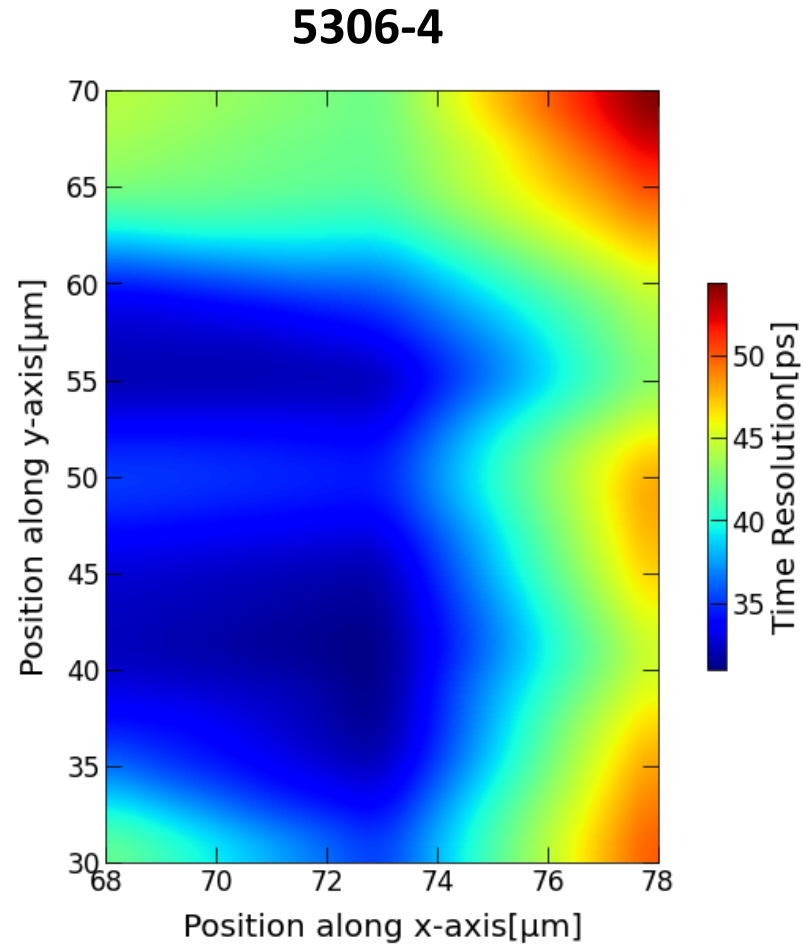


# Time Resolution: Unirradiated 3D Pixel Sensors

- Low laser intensity – MPV around 80-110 mV, low compared to beta set-up (145 mV)
- Cell structure not as clear as for time resolution, but still fits the expectations
- Rise time between 340 and 420 ps, higher than measured in the beta set-up



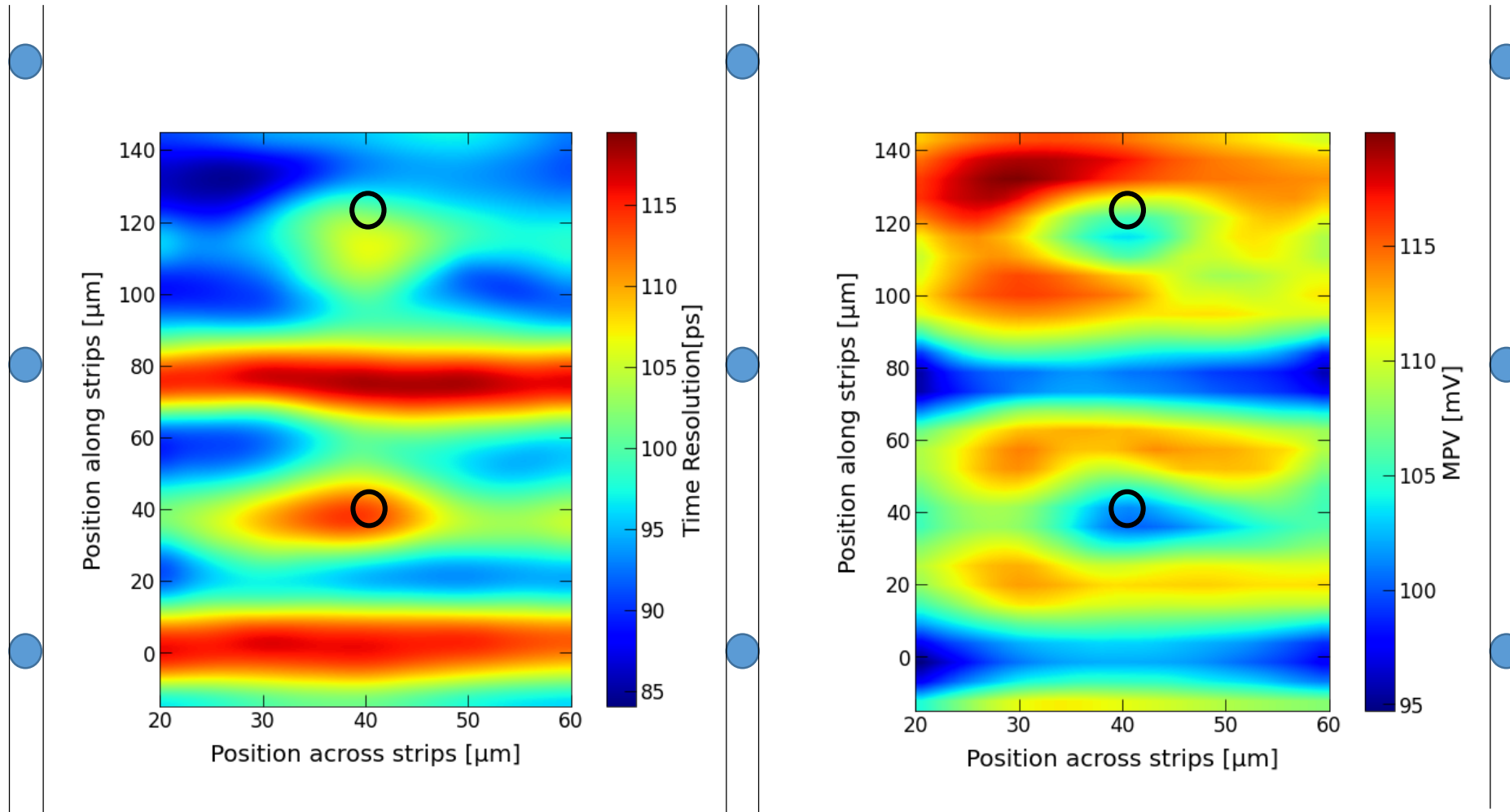
# 3D Pixel sensors



Expected voltage dependence

# Time Resolution: 3D Strip Sensor 2

5936-4 Strip Sensor: 285  $\mu\text{m}$  thick, high leakage current (sensor broken in half), measured at 40 V



- Clear cell structure
- Worse resolution ● between junction columns
- Worse resolution around ohmic columns ○
- Resolution correlates to the expected el. Field
- Resolution between 85 and 115 ps  $\rightarrow$  lower voltage, higher noise
- Correlation also to MPV